

Kenji Nomura

List of Publications by Citations

Source: <https://exaly.com/author-pdf/3729879/kenji-nomura-publications-by-citations.pdf>

Version: 2024-04-20

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

96
papers

17,509
citations

47
h-index

101
g-index

101
ext. papers

19,081
ext. citations

5.1
avg, IF

6.4
L-index

#	Paper	IF	Citations
96	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. <i>Nature</i> , 2004 , 432, 488-92	50.4	5517
95	Thin-film transistor fabricated in single-crystalline transparent oxide semiconductor. <i>Science</i> , 2003 , 300, 1269-72	33.3	1534
94	Present status of amorphous In-Ga-Zn-O thin-film transistors. <i>Science and Technology of Advanced Materials</i> , 2010 , 11, 044305	7.1	1287
93	High-mobility thin-film transistor with amorphous InGaZnO ₄ channel fabricated by room temperature rf-magnetron sputtering. <i>Applied Physics Letters</i> , 2006 , 89, 112123	3.4	944
92	Giant thermoelectric Seebeck coefficient of a two-dimensional electron gas in SrTiO ₃ . <i>Nature Materials</i> , 2007 , 6, 129-34	27	794
91	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 4303-4308	1.4	589
90	p-channel thin-film transistor using p-type oxide semiconductor, SnO. <i>Applied Physics Letters</i> , 2008 , 93, 032113	3.4	491
89	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO ₄ . <i>Thin Solid Films</i> , 2005 , 486, 38-41	2.2	385
88	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. <i>Journal of Display Technology</i> , 2009 , 5, 273-288		371
87	Modeling of amorphous InGaZnO ₄ thin film transistors and their subgap density of states. <i>Applied Physics Letters</i> , 2008 , 92, 133503	3.4	289
86	Subgap states in transparent amorphous oxide semiconductor, InGaZnO, observed by bulk sensitive x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 202117	3.4	268
85	Trap densities in amorphous-InGaZnO ₄ thin-film transistors. <i>Applied Physics Letters</i> , 2008 , 92, 133512	3.4	254
84	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O ₂ annealing. <i>Applied Physics Letters</i> , 2008 , 93, 192107	3.4	243
83	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO ₃ (ZnO) ₅ films. <i>Applied Physics Letters</i> , 2004 , 85, 1993-1995	3.4	229
82	Ambipolar oxide thin-film transistor. <i>Advanced Materials</i> , 2011 , 23, 3431-4	24	207
81	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in InGaZnO system. <i>Applied Physics Letters</i> , 2007 , 90, 242114	3.4	200
80	Epitaxial growth of high mobility Cu ₂ O thin films and application to p-channel thin film transistor. <i>Applied Physics Letters</i> , 2008 , 93, 202107	3.4	193

79	Tin monoxide as an s-orbital-based p-type oxide semiconductor: Electronic structures and TFT application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2187-2191	1.6	185
78	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. <i>Journal of Display Technology</i> , 2009 , 5, 462-467		185
77	Specific contact resistances between amorphous oxide semiconductor InGaZnO and metallic electrodes. <i>Thin Solid Films</i> , 2008 , 516, 5899-5902	2.2	171
76	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. <i>Applied Physics Letters</i> , 2010 , 97, 072111	3.4	165
75	Amorphous oxide channel TFTs. <i>Thin Solid Films</i> , 2008 , 516, 1516-1522	2.2	155
74	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2796-2800	3.9	152
73	Amorphous InGaZnO coplanar homojunction thin-film transistor. <i>Applied Physics Letters</i> , 2009 , 94, 133502	3.4	150
72	Growth, structure and carrier transport properties of Ga ₂ O ₃ epitaxial film examined for transparent field-effect transistor. <i>Thin Solid Films</i> , 2006 , 496, 37-41	2.2	142
71	Frontier of transparent oxide semiconductors. <i>Solid-State Electronics</i> , 2003 , 47, 2261-2267	1.7	123
70	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. <i>Applied Physics Letters</i> , 2010 , 96, 122103	3.4	121
69	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. <i>IEEE Electron Device Letters</i> , 2007 , 28, 273-275	4.4	104
68	Electronic Defects in Amorphous Oxide Semiconductors: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800372	1.6	103
67	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 202114	3.4	92
66	Photofield-effect in amorphous In-Ga-Zn-O (a-IGZO) thin-film transistors. <i>Journal of Information Display</i> , 2008 , 9, 21-29	4.1	82
65	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-InGaZnO and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. <i>Applied Physics Letters</i> , 2010 , 96, 263509	3.4	81
64	Device characteristics improvement of a-InGaZnO TFTs by low-temperature annealing. <i>Thin Solid Films</i> , 2010 , 518, 3017-3021	2.2	80
63	Unusually large enhancement of thermopower in an electric field induced two-dimensional electron gas. <i>Advanced Materials</i> , 2012 , 24, 740-4	24	71
62	Stability and high-frequency operation of amorphous InGaZnO thin-film transistors with various passivation layers. <i>Thin Solid Films</i> , 2012 , 520, 3778-3782	2.2	69

61	. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1695-1697	4.4	69
60	Effects of post-annealing on (110) Cu ₂ O epitaxial films and origin of low mobility in Cu ₂ O thin-film transistor. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2192-2197	1.6	59
59	Optical and Carrier Transport Properties of Cosputtered ZnInSn Films and Their Applications to TFTs. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H390	3.9	57
58	Large Photoresponse in Amorphous InGaZn and Origin of Reversible and Slow Decay. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H324		54
57	Growth mechanism for single-crystalline thin film of InGaO ₃ (ZnO) ₅ by reactive solid-phase epitaxy. <i>Journal of Applied Physics</i> , 2004 , 95, 5532-5539	2.5	54
56	Interactive radical dimers in photoconductive organic thin films. <i>Angewandte Chemie - International Edition</i> , 2009 , 48, 4022-4	16.4	50
55	Amorphous InGaZn-O thin-film transistor with coplanar homojunction structure. <i>Thin Solid Films</i> , 2009 , 518, 1309-1313	2.2	50
54	Intrinsic carrier mobility in amorphous InGaZn thin-film transistors determined by combined field-effect technique. <i>Applied Physics Letters</i> , 2010 , 96, 262105	3.4	48
53	Field-modulated thermopower in SrTiO ₃ -based field-effect transistors with amorphous 12CaO \cdot 7Al ₂ O ₃ glass gate insulator. <i>Applied Physics Letters</i> , 2009 , 95, 113505	3.4	48
52	Simple Analytical Model of On Operation of Amorphous InGaZn Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3463-3471	2.9	47
51	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. <i>Thin Solid Films</i> , 2010 , 518, 3012-3016	2.2	45
50	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3085-Q3090		43
49	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous InGaZn Channels. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H197		43
48	Device applications of transparent oxide semiconductors: Excitonic blue LED and transparent flexible TFT. <i>Journal of Electroceramics</i> , 2006 , 17, 267-275	1.5	41
47	Amorphous InGaZn Dual-Gate TFTs: Current-Voltage Characteristics and Electrical Stress Instabilities. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1928-1935	2.9	40
46	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaO \cdot 7Al ₂ O ₃ . <i>Chemistry of Materials</i> , 2005 , 17, 6311-6316	9.6	39
45	Novel film growth technique of single crystalline In ₂ O ₃ (ZnO) _m (m=integer) homologous compound. <i>Thin Solid Films</i> , 2002 , 411, 147-151	2.2	35
44	Control of carrier concentration and surface flattening of CuGaO ₂ epitaxial films for a p-channel transparent transistor. <i>Thin Solid Films</i> , 2008 , 516, 5790-5794	2.2	32

43	Effects of low-temperature ozone annealing on operation characteristics of amorphous InGaZnO thin-film transistors. <i>Thin Solid Films</i> , 2012 , 520, 3787-3790	2.2	30
42	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. <i>Applied Physics Letters</i> , 2013 , 103, 201904	3.4	26
41	Hydrogen-Defect Termination in SnO for p-Channel TFTs. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 1162-1168	4.1	23
40	Orientation control of zinc oxide films by pulsed current electrolysis. <i>Journal of Crystal Growth</i> , 2002 , 235, 224-228	1.6	22
39	Preparation of Zinc Oxide Thin Films by Pulsed Current Electrolysis. <i>Journal of the Electrochemical Society</i> , 2002 , 149, F76	3.9	20
38	Anisotropic carrier transport properties in layered cobaltate epitaxial films grown by reactive solid-phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 94, 152105	3.4	19
37	Photovoltaic properties of n-type amorphous InGaZnO and p-type single crystal Si heterojunction solar cells: Effects of Ga content. <i>Thin Solid Films</i> , 2012 , 520, 3808-3812	2.2	18
36	Self-Adjusted, Three-Dimensional Lattice-Matched Buffer Layer for Growing ZnO Epitaxial Film: Homologous Series Layered Oxide, InGaO ₃ (ZnO) ₅ . <i>Crystal Growth and Design</i> , 2006 , 6, 2451-2456	3.5	18
35	All oxide transparent MISFET using high-k dielectrics gates. <i>Microelectronic Engineering</i> , 2004 , 72, 294-298	3.5	18
34	Examination of the ambient effects on the stability of amorphous indium-gallium-zinc oxide thin film transistors using a laser-glass-sealing technology. <i>Applied Physics Letters</i> , 2014 , 105, 133503	3.4	16
33	Steady-state photoconductivity of amorphous InGaZnO. <i>Thin Solid Films</i> , 2010 , 518, 3000-3003	2.2	16
32	Back-Channel Defect Termination by Sulfur for p-Channel CuO Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 51581-51588	9.5	15
31	Frequency- and Power-Dependent Photoresponse of a Perovskite Photodetector Down to the Single-Photon Level. <i>Nano Letters</i> , 2020 , 20, 2144-2151	11.5	15
30	. <i>Journal of Display Technology</i> , 2014 , 10, 979-983		15
29	In situ Observation of the Crystallization Process of Ferroelectric Thin Films by Raman Microspectroscopy. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 5247-5251	1.4	15
28	Switching Mechanism behind the Device Operation Mode in SnO-TFT. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000742	6.4	13
27	Epitaxial film growth and superconducting behavior of sodium-cobalt oxyhydrate, Na _x CoO ₂ ·yH ₂ O (x approximately 0.3, y approximately 1.3). <i>Inorganic Chemistry</i> , 2006 , 45, 1894-6	5.1	13
26	Growth and structure of heteroepitaxial thin films of homologous compounds RAO ₃ (MO) _m by reactive solid-phase epitaxy: Applicability to a variety of materials and epitaxial template layers. <i>Thin Solid Films</i> , 2006 , 496, 64-69	2.2	13

25	Growth of epitaxial ZnO thin films on lattice-matched buffer layer: Application of InGaO ₃ (ZnO) ₆ single-crystalline thin film. <i>Thin Solid Films</i> , 2005 , 486, 28-32	2.2	13
24	Operation model with carrier-density dependent mobility for amorphous InGaZnO thin-film transistors. <i>Thin Solid Films</i> , 2012 , 520, 3791-3795	2.2	11
23	Electron transport in InGaO ₃ (ZnO) _m (m=integer) studied using single-crystalline thin films and transparent MISFETs. <i>Thin Solid Films</i> , 2003 , 445, 322-326	2.2	11
22	Electronic Structure and Photovoltaic Properties of n-Type Amorphous In-Ga-Zn-O and p-Type Single Crystal Si Heterojunctions. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H346		10
21	Threshold switching of non-stoichiometric CuO nanowire for selector application. <i>Applied Physics Letters</i> , 2020 , 116, 023503	3-4	9
20	Artificial Synapse Based on a 2D-SnO Memtransistor with Dynamically Tunable Analog Switching for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2021 ,	9-5	9
19	Recent progress of oxide-TFT-based inverter technology. <i>Journal of Information Display</i> , 1-19	4-1	9
18	Light Irradiation History Sensor Using Amorphous In-Ga-Zn-O Thin-Film Transistor Exposed to Ozone Annealing. <i>IEEE Electron Device Letters</i> , 2012 , 33, 384-386	4-4	6
17	Excimer laser crystallization of InGaZnO ₄ on SiO ₂ substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 1694-1696	2-1	6
16	Epitaxial film growth, optical, electrical, and magnetic properties of layered oxide In ₃ FeTi ₂ O ₁₀ . <i>Journal of Applied Physics</i> , 2007 , 101, 103714	2-5	6
15	Atomically Thin Tin Monoxide-Based p-Channel Thin-Film Transistor and a Low-Power Complementary Inverter. <i>ACS Applied Materials & Interfaces</i> , 2021 ,	9-5	6
14	Fabrication of Atomically Flat ScAlMgO ₄ Epitaxial Buffer Layer and Low-Temperature Growth of High-Mobility ZnO Films. <i>Crystal Growth and Design</i> , 2010 , 10, 1084-1089	3-5	5
13	Large domain growth of GaN epitaxial films on lattice-matched buffer layer ScAlMgO ₄ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 161, 66-70	3-1	5
12	Maximum applied voltage detector using amorphous InGaZnO thin-film transistor exposed to ozone annealing. <i>Solid-State Electronics</i> , 2012 , 75, 74-76	1-7	4
11	Fabrication of ScAlMgO ₄ epitaxial thin films using ScGaO ₃ (ZnO) _m buffer layers and its application to lattice-matched buffer layer for ZnO epitaxial growth. <i>Thin Solid Films</i> , 2008 , 516, 5842-5846	2-2	4
10	Fabrication of GaN epitaxial thin film on InGaZnO ₄ single-crystalline buffer layer. <i>Thin Solid Films</i> , 2010 , 518, 2996-2999	2-2	3
9	Resistive switching memory effects in p-type hydrogen-treated CuO nanowire. <i>Applied Physics Letters</i> , 2020 , 117, 043502	3-4	3
8	Voltage Transfer Characteristics of CMOS-Like Inverters for Ambipolar SnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2022 , 43, 52-55	4-4	2

7	P.3: 3-D Stacked Complementary TFT Devices using n-type HfGZO and p-type F8T2 TFTs □ Operation Confirmation of NOT and NAND Logic Circuits □ <i>Digest of Technical Papers SID International Symposium, 2013</i> , 44, 995-998	0.5	1
6	8-3: Invited Paper: Back-Channel Defect Termination for p-Channel Oxide-TFTs. <i>Digest of Technical Papers SID International Symposium, 2021</i> , 52, 85-88	0.5	1
5	Solid-phase epitaxial growth of (111)-oriented Si film on InGaO3(ZnO)5 buffer layer. <i>Journal of Materials Science: Materials in Electronics, 2011</i> , 22, 920-923	2.1	
4	????????? TFT ?????????????????????????????????? TFT ??. <i>Seikei-Kakou, 2005</i> , 17, 588-592	0	
3	P-2: Hydrogenated SnO for p-channel oxide Thin Film Transistor. <i>Digest of Technical Papers SID International Symposium, 2020</i> , 51, 1315-1318	0.5	
2	Toward the Development of High-Performance p -Channel Oxide-TFTs and All-Oxide Complementary Circuits 2022 , 519-538		
1	Defects and Relevant Properties 2022 , 93-103		